Amendments to the Specification:

Please replace paragraph beginning at page 8, line 4 with the following rewritten paragraph:

Still other gases include diborane (B_2H_6); phosphine (PH_3); and carbon-silicon compounds such as methylsilane (CH_3SiH_3) and hexamethyldisilane ($(CH_3)_3Si\text{-}Si(CH_3)_3$; and hexamethyldisilazane (HMDS). Additional alternate embodiments of the current invention use hydrazine (N_2H_4), monomethylhydrazine, carbon tetrafluoride (CF_4), CHF_3, HCl, and boron trichloride (BCl_3), which are also useful in passivating dielectrics, as addressed in copending application 09/114,847, now issued as U.S. Patent No. 6,201,276 B1. Also included are mixtures of any of the gases or types of gases described above. Exemplary non-plasma process parameters using these other gases include a flow rate of about 2 sccm to about 400 sccm for these gases; a flow rate of about 50 sccm to about 100 sccm for an inert carrier gas such as He or Ar; a temperature ranging from about 150 to about 600 degrees Celsius, a pressure ranging from about 50 millitorr to about 1 atmosphere (760 torr); and a process time ranging from about 50 to about 500 seconds. Again, one skilled in the art is aware that these parameters can be altered to achieve the same or a similar process.

Amend the specification by inserting a new section before the "Technical Field" as follows:

-- CROSS-REFERENCE TO RELATED APPLICATIONS

This application is a continuation of pending United States Patent Application No. 09/652,994, filed August 31, 2000, which is a divisional of United States Patent Application No. 09/200,253, filed November 25, 1998, United States Patent No. 6,303,972, issued on October 16, 2001.--